

BUK768R1-100E,118 Datasheet



DiGi Electronics Part Number	
Manufacturer	
Manufacturer Product Number	
Description	

Detailed Description

BUK768R1-100E,118-DG

Nexperia USA Inc.

BUK768R1-100E,118

MOSFET N-CH 100V 100A D2PAK

N-Channel 100 V 100A (Tc) 263W (Tc) Surface Moun t D2PAK

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Purchase and inquiry

Manufacturer Product Number:	Manufacturer:
BUK768R1-100E,118	Nexperia USA Inc.
Series:	Product Status:
TrenchMOS™	Obsolete
FET Type:	Technology:
N-Channel	MOSFET (Metal Oxide)
Drain to Source Voltage (Vdss):	Current - Continuous Drain (Id) @ 25°C:
100 V	100A (Tc)
Drive Voltage (Max Rds On, Min Rds On):	Rds On (Max) @ ld, Vgs:
10V	8.1mOhm @ 25A, 10V
Vgs(th) (Max) @ ld:	Gate Charge (Qg) (Max) @ Vgs:
4V @ 1mA	108 nC @ 10 V
Vgs (Max):	Input Capacitance (Ciss) (Max) @ Vds:
±20V	7380 pF @ 25 V
FET Feature:	Power Dissipation (Max):
	263W (Tc)
Operating Temperature:	Grade:
-55°C ~ 175°C (TJ)	Automotive
Qualification:	Mounting Type:
AEC-Q101	Surface Mount
Supplier Device Package:	Package / Case:
D2PAK	TO-263-3, D2PAK (2 Leads + Tab), TO-263AB
Base Product Number:	
BUK768	

Environmental & Export classification

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	
8541.29.0095	



BUK768R1-100E

N-channel TrenchMOS standard level FET 5 October 2012

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C

1.3 Applications

- 12V, 24V and 48V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

1.4 Quick reference data

Table 1. C							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	100	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 1</u>	[1]	-	-	100	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	263	W
Static chara	acteristics	·					
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11		-	6.4	8.1	mΩ
Dynamic ch	haracteristics	·					
Q _{GD}	gate-drain charge	V_{GS} = 10 V; I _D = 25 A; V _{DS} = 80 V; T _j = 25 °C; Fig. 13; Fig. 14		-	38.6	-	nC

Table 1. Quick reference data

[1] Continuous current is limited by package.

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BUK768R1-100E

N-channel TrenchMOS standard level FET

2. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D
2	D	drain		
3	S	source		G-UT 4
mb	D	mounting base; connected to drain		mbb076 S
			D2PAK (SOT404)	

3. Ordering information

Table 3. Ordering inf	formation		
Type number	Package		
	Name	Description	Version
BUK768R1-100E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Marking

Table 4. Marking codes	
Type number	Marking code
BUK768R1-100E	BUK768R1-100E

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	100	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ		-	100	V
V _{GS}	gate-source voltage	T _j ≤ 175 °C; DC		-20	20	V
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 1</u>	[1]	-	100	А
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 1</u>		-	78	А
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 4		-	439	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 2</u>		-	263	W
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
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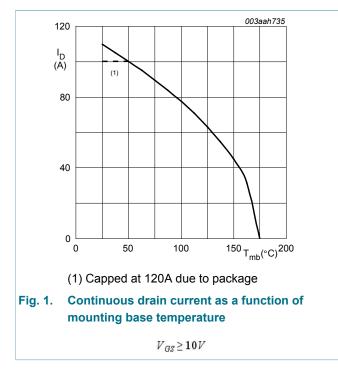
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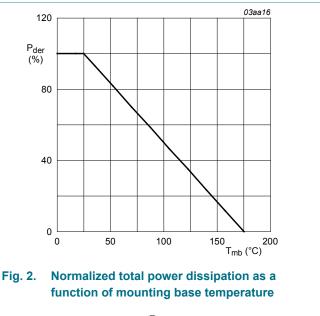
Symbol	Parameter	Conditions		Min	Max	Unit
Source-drain	Source-drain diode					
I _S	source current	T _{mb} = 25 °C	[1]	-	100	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	439	А
Avalanche ru	ggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:ID} \begin{array}{l} I_{D} = 100 \; \text{A}; V_{sup} \leq 100 \; \text{V}; \text{R}_{GS} = 50 \; \Omega; \\ V_{GS} = 10 \; \text{V}; \; \text{T}_{j(init)} = 25 \; ^{\circ}\text{C}; \; \text{unclamped}; \\ \hline \text{Fig. 3} \end{array}$	[2][3]	-	219	mJ

[1]

Continuous current is limited by package. Single-pulse avalanche rating limited by maximum junction temperature of 175 °C. [2]

[3] Refer to application note AN10273 for further information.

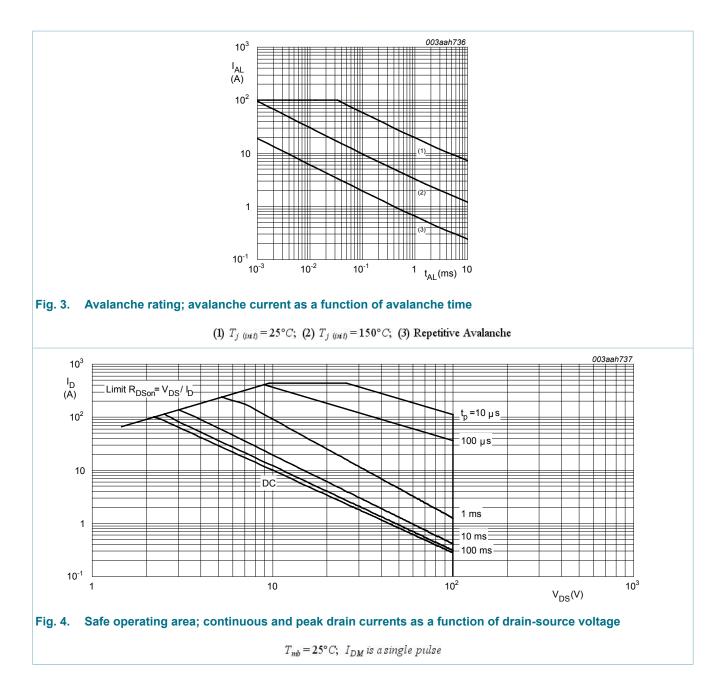




$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

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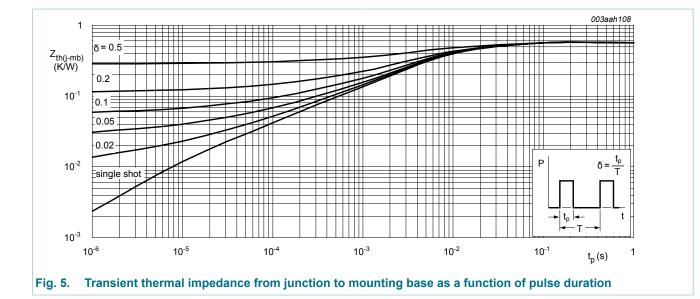


6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	-	0.57	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed-circuit board	-	50	-	K/W

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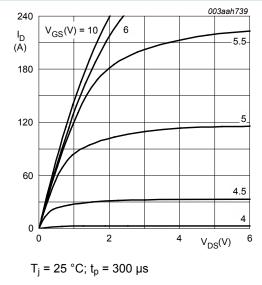
Characteristics 7.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics	1				
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	100	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	90	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 9; Fig. 10	2.4	3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 9	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	4.5	V
I _{DSS} drain	drain leakage current	V_{DS} = 100 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	1	μA
		V_{DS} = 100 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = 20 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	6.4	8.1	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	21.9	mΩ
Dynamic ch	naracteristics	· · ·				
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 80 \text{ V}; V_{GS} = 10 \text{ V};$	-	108	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 13</u> ; <u>Fig. 14</u>	-	22.8	-	nC
Q _{GD}	gate-drain charge		-	38.6	-	nC

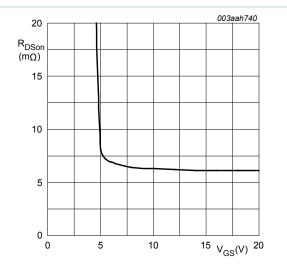
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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;		-	5535	7380	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 15</u>		-	521	625	pF
C _{rss}	reverse transfer capacitance			-	352	482	pF
t _{d(on)}	turn-on delay time	V_{DS} = 80 V; R _L = 3.2 Ω; V _{GS} = 10 V;		-	23.5	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega$		-	44.1	-	ns
t _{d(off)}	turn-off delay time			-	72	-	ns
t _f	fall time			-	49.6	-	ns
L _D	internal drain inductance	from upper edge of mounting base to centre of die		-	2.5	-	nH
L _S	internal source inductance	measured from source lead to source bond pad ; $T_j = 25 \ ^{\circ}C$		-	7.5	-	nH
Source-dra	in diode		I				
V _{SD}	source-drain voltage	I_{S} = 25 A; V_{GS} = 0 V; T_{j} = 25 °C; Fig. 16		-	0.82	1.2	V
t _{rr}	reverse recovery time	$I_{\rm S}$ = 20 A; dI_{\rm S}/dt = -100 A/µs; V _{GS} = 0 V;		-	55	-	ns
Qr	recovered charge	V _{DS} = 25 V		-	134	-	nC





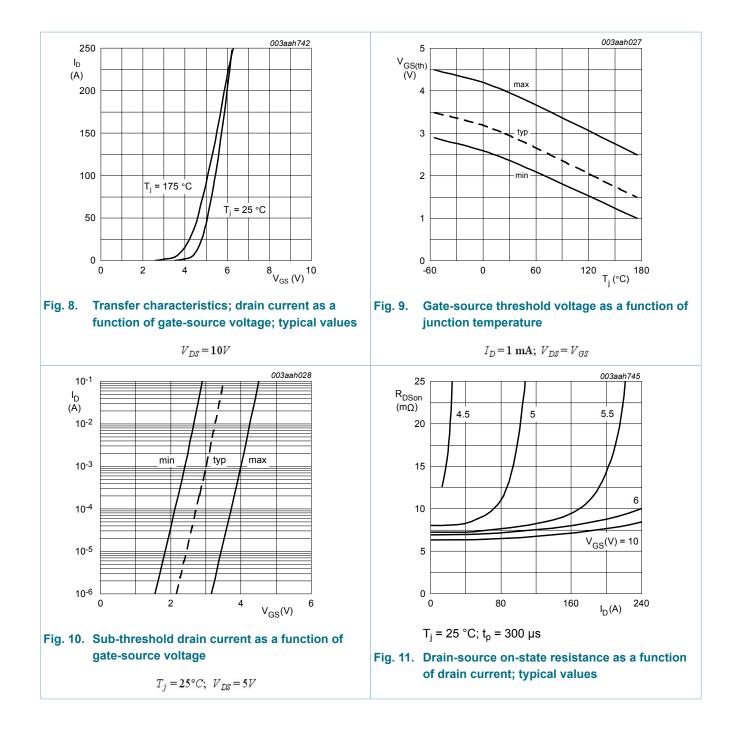




 $T_j = 25^{\circ}C; \ I_D = 25A$

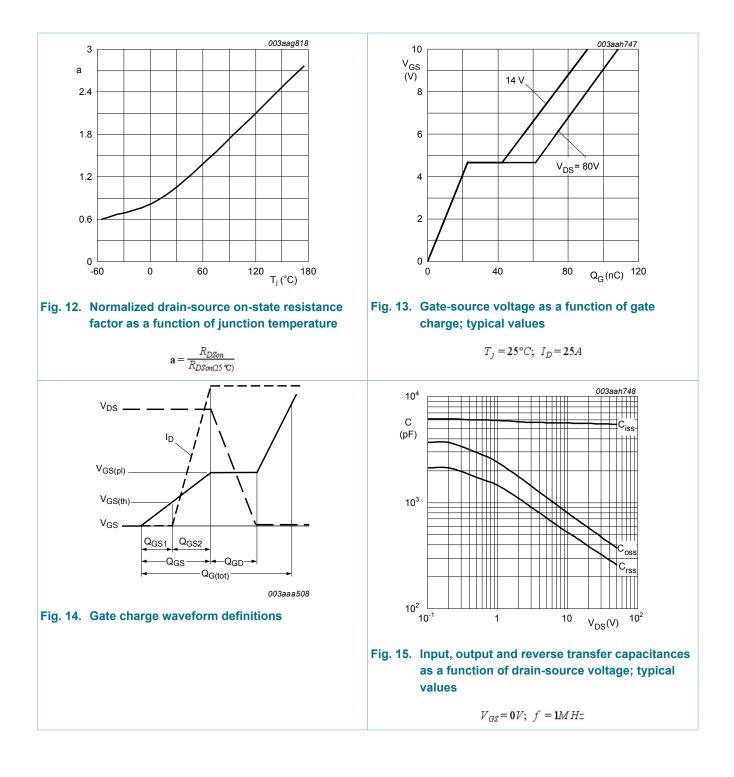
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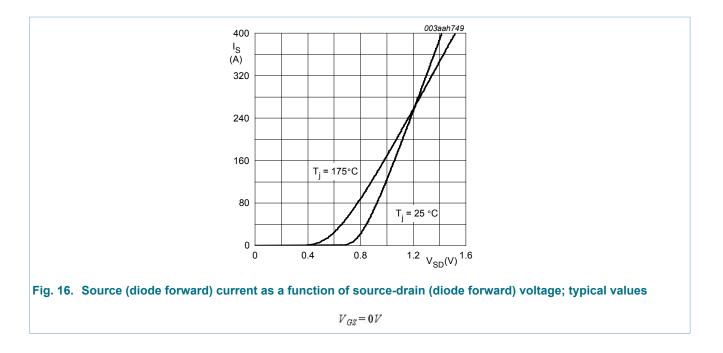
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8. Package outline

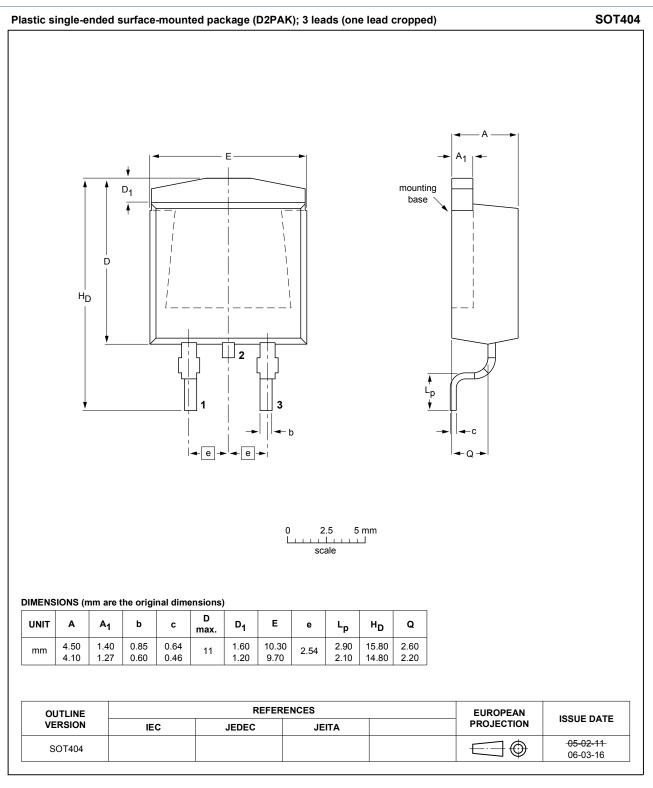


Fig. 17. Package outline D2PAK (SOT404)

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Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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10. Contents

1	Product profile	1
1.1	General description	1
1.2	Features and benefits	1
1.3	Applications	1
1.4	Quick reference data	1
2	Pinning information	2
3	Ordering information	2
4	Marking	2
5	Limiting values	2
6	Thermal characteristics	4
7	Characteristics	5
8	Package outline	10
9	Legal information	11
9.1	Data sheet status	11
9.2	Definitions	11
9.3	Disclaimers	11
9.4	Trademarks	12

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